Elektronische Bauelemente

2SB1151

-5 A , -60 V

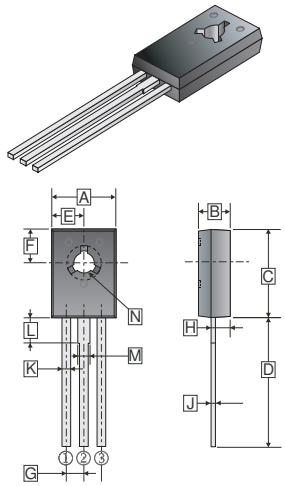
PNP Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead free

FEATURES

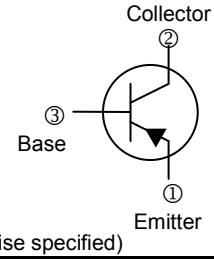
- Low Collector-Emitter Saturation Voltage
- Large Collector Current
- High Power Dissipation

TO-126



ORDER INFORMATION

Part Number	Type
2SB1151-Y	Lead (Pb)-free
2SB1151-Y-C	Lead (Pb)-free and Halogen-free



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	7.40	7.80	H	1.10	1.50
B	2.50	2.90	J	0.45	0.60
C	10.60	11.00	K	0.66	0.86
D	15.30	15.70	L	2.10	2.30
E	3.70	3.90	M	1.17	1.37
F	3.90	4.10	N	3.00	3.20
G	2.29 TYP.				

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current-Continuous	I_C	-5	A
Collector Power Dissipation	P_C	1.25	W
Maximum Junction to Ambient	$R_{\theta JA}$	100	°C/W
Junction, Storage Temperature	T_J, T_{STG}	-55~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60	-	-	V	I_C= -100μA, I_E=0
Collector-Emitter Breakdown voltage	$V_{(BR)CEO}$	-60	-	-	V	I_C= -1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-7	-	-	V	I_C=0, I_E= -100μA
Collector Cut-Off Current	I_{CBO}	-	-	-10	μA	V_{CB}= -50V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	-10	μA	V_{EB}= -7V, I_C=0
DC Current Gain	$h_{FE(1)}$	160	-	320		V_{CE}= -1V, I_C= -2A
	$h_{FE(2)}$	60	-	-		V_{CE}= -1V, I_C= -0.1A
	$h_{FE(3)}$	50	-	-		V_{CE}= -2V, I_C= -5A
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	-0.3	V	I_C= -2A, I_B = -0.2A
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-	-	-1.2	V	I_C= -2A, I_B = -0.2A

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CHARACTERISTIC CURVES